

**SEMICONDUCTOR DEVICES HAVING CAPACITORS OF METAL-  
INSULATOR-METAL STRUCTURE WITH COEXTENSIVE OXIDATION  
BARRIER PATTERN AND LOWER ELECTRODE BOTTOM AND  
METHODS OF FORMING THE SAME**

Related Application

This application claims priority to Korean Patent Application 2002-66520,  
filed on October 30, 2002, the content of which is incorporated by reference herein in  
5 its entirety.

Field of the Invention

The present invention relates to a semiconductor device and a method of  
forming the same. More particularly, the present invention is directed to a  
10 semiconductor device having capacitors of a metal-insulator-metal structure and a  
method of forming the same.

Background of the Invention

A typical capacitor includes a lower electrode, an upper electrode and a  
15 dielectric film interposed therebetween. Since the capacitor accumulates charges, it  
has been used for data storage in semiconductor memory devices. One type of  
semiconductor memory device is DRAM ("dynamic random access memory") which  
can form a unit cell having one transistor for inputting/outputting data and one  
capacitor for storing the data.

20 Unfortunately, with present trends toward high integration of semiconductor  
devices, the capacitance of semiconductor capacitors may continue to decrease. One  
technique which has been proposed to solve this problem is to use a dielectric film of  
a capacitor that has a higher dielectric value than oxide-nitride-oxide (ONO).  
However, the dielectric film can undesirably react on the lower electrode to  
25 deteriorate a capacitor characteristic (*e.g.*, leakage current). In order to overcome the

potential deterioration of the capacitor characteristic, a capacitor having a metal-insulator-metal (MIM) structure (hereinafter referred to as "MIM capacitor") has been proposed. The MIM capacitor includes a lower electrode, an upper electrode, and a metal layer (particularly, noble metal layer) to reduce the capacitor leakage current.

5 Further, the MIM capacitor may constitute the unit cell of a ferroelectric memory device. Similar to a DRAM unit cell, the unit cell of the ferroelectric memory includes one transistor and one capacitor. A difference therebetween is that the capacitor of the ferroelectric memory device has a dielectric film made of ferroelectric. Since the ferroelectric film has a polarization hysteresis characteristic, a  
10 capacitor using the ferroelectric film can retain its stored data even when its power supply is interrupted.

When fabricating a semiconductor device having the MIM capacitor, an oxidation barrier pattern is conventionally formed between a lower electrode and an underlying contact plug. During an annealing process for crystallizing a high-k  
15 dielectric film or a ferroelectric film, the lower electrode or the contact plug may be oxidized to increase contact resistance. The oxidation barrier pattern can reduce the increase of the annealing-induced contact resistance.

A first conventional method for forming a lower electrode of a conventional MIM capacitor is described below with reference to **FIG. 1** and **FIG. 2**. Another  
20 conventional method for forming a lower electrode and an oxidation barrier pattern of a conventional MIM capacitor is described below with reference to **FIG. 3**.

Referring to **FIG. 1** and **FIG. 2**, a lower interlayer dielectric **2** is formed on a semiconductor substrate **1**. Buried contact plugs **3** are formed through the lower interlayer dielectric **2** to connect to a predetermined region of the semiconductor  
25 substrate **1**. An oxidation barrier pattern **4** is formed over a top surface of the buried contact plug **3**. An upper interlayer dielectric **5** is formed on an entire surface of a semiconductor substrate including the oxidation barrier pattern **4**. The upper interlayer dielectric **5** is patterned to form a lower electrode recess **6** exposing a predetermined region of the oxidation barrier pattern **4**. A lower electrode layer **7** is  
30 formed on an entire surface of the semiconductor substrate **1** including an inside of the lower electrode recess **6**. A sacrificial insulating layer **8** is formed on the lower electrode layer **7** to fill the lower electrode recess **6**. The lower electrode layer **7** is made of metal. As shown in **FIG. 2**, the sacrificial insulating layer **8** and the lower electrode layer **7** are planarized down to a top surface of the upper interlayer dielectric

5 to form a lower electrode 7a and a sacrificial insulating pattern 8a which are sequentially stacked in the lower electrode recess 6.

In view of a design constraint, the oxidation barrier pattern 4 is minimally spaced apart from an adjacent oxidation barrier pattern 4. The lower electrode recess 6 may not entirely expose the top surface of the oxidation barrier pattern 4 because of an alignment margin 10 between the lower electrode recess 6 and the oxidation barrier pattern 4. That is, the top surface of the oxidation barrier pattern 4 has an area which is obtained by adding an area corresponding to the bottom surface of the lower electrode 7a to the area corresponding to the alignment margin(s) 10 of the oxidation barrier pattern 4. Accordingly, the surface area of the lower electrode 7a may be smaller than that of a lower electrode formed without the oxidation barrier pattern 4.

Referring to FIG. 3, the buried contact plug 3 is formed through the lower interlayer dielectric 2 to the semiconductor substrate 1. The buried contact plug 3 is connected to a predetermined region of the semiconductor substrate 1. The upper interlayer dielectric 5 is formed on an entire surface of a semiconductor substrate 1 including the buried contact plug 3. The upper interlayer dielectric layer 5 is patterned to form a lower electrode recess 6 exposing a top surface of the interlayer dielectric 5. An oxidation barrier layer (not shown) and a lower electrode layer (not shown) are sequentially formed on an entire surface of a semiconductor substrate 1 including an inside of the lower electrode recess 6. A sacrificial insulating layer (not shown) is formed on the lower electrode layer to fill the lower electrode recess 6. The sacrificial insulating layer, the lower electrode layer, and the oxidation barrier layer are sequentially planarized down to a top surface of the interlayer dielectric 5 to form an oxidation barrier pattern 4a, the lower electrode 7a, and a sacrificial insulating pattern 8a which are sequentially stacked in the lower electrode recess 6.

The oxidation barrier pattern 4a is also formed on a bottom side and sidewalls of the lower electrode 7a. In this case, a surface area of the lower electrode 7a is smaller than that of a lower electrode without the oxidation barrier pattern 4b. This is because the oxidation barrier layer 4a is formed on the sidewalls of the lower electrode 7a to thereby reduce the size of the lower electrode 7a.

#### Summary of the Invention

In certain embodiments, the present invention provides semiconductor devices that include an interlayer dielectric formed on a semiconductor substrate. A buried

contact plug is disposed through the interlayer dielectric to be connected to a predetermined region of the semiconductor substrate. An oxidation barrier pattern is disposed on a top surface of the buried contact plug. A portion of a lower electrode is disposed on the oxidation barrier pattern. A top surface area of the oxidation barrier  
5 pattern is substantially equal to a bottom surface area of the lower electrode.

In particular embodiments, an external sidewall of the lower electrode and a sidewall of the oxidation barrier pattern are disposed in a beeline (*i.e.*, in a substantially straight line). An upper electrode can be disposed over the lower electrode with a dielectric film therebetween. The dielectric film may be made of a  
10 high-k (dielectric coefficient) value dielectric substance that has a higher dielectric constant value than oxide-nitride-oxide (ONO). The dielectric film may be made of a ferroelectric material.

Other embodiments are directed to a method of fabricating a semiconductor device. The method includes forming an oxidation barrier pattern and a capping layer  
15 pattern which are sequentially stacked on a semiconductor substrate. A mold insulating layer having an etch selectivity with respect to the capping layer pattern is formed on a semiconductor substrate including the capping layer pattern. The mold insulating layer can be removed and/or planarized down to a top surface of the capping layer pattern. The exposed capping layer pattern is etched to form a lower  
20 electrode recess exposing an entire top surface of the oxidation barrier pattern to form a lower electrode in the lower electrode recess. In this case, the capping layer pattern is made of a material having an etch selectivity with respect to the oxidation barrier pattern.

In certain embodiments, the capping layer pattern can be made of silicon  
25 nitride. Following formation of the lower electrode, the method can further include etching the mold insulating layer to be removed and sequentially stacking a dielectric film and an upper electrode on the lower electrode. The dielectric film may be made of a dielectric substance having a higher dielectric constant than oxide-nitride-oxide (ONO). The dielectric film may be made of a ferroelectric material.

30 Certain embodiments are directed to a MIM capacitor including: (a) semiconductor substrate; (b) an oxidation barrier pattern residing above and in electrical communication with the semiconductor substrate, wherein the oxidation barrier pattern defines a lower electrode platform with a top surface; (c) a lower electrode having a bottom and at least one sidewall, the bottom being disposed on the

oxidation barrier pattern lower electrode platform; (d) an upper electrode in spaced apart alignment with the lower electrode; and (e) a dielectric layer interposed between the upper and lower electrodes. The lower electrode bottom has a surface area that is substantially coextensive with the surface area of the top surface of the oxidation barrier pattern lower electrode platform.

Additional embodiments are directed toward a semiconductor device having a plurality of capacitors of a metal-insulator-metal structure. The capacitors each include upper electrodes, lower electrodes and a dielectric layer interposed therebetween. The capacitors reside above a semiconductor substrate with each capacitor having a corresponding oxidation barrier pattern in electrical communication with respective regions of the semiconductor substrate. The device is configured so that the lower electrodes have a bottom surface area that is substantially equal to the surface area of the upper surface of the underlying oxidation barrier pattern.

In certain embodiments, the lower electrode is substantially cylindrical with a closed continuous surface bottom. The device may be suitable to define a portion of an integrated circuit, such as the unit cell of a DRAM memory device and/or a unit cell of a ferroelectric memory device.

Other embodiments are directed to methods for fabricating a semiconductor device with a plurality of MIM capacitors in unit cells of an integrated circuit memory device. The method includes forming an oxidation barrier pattern on a semiconductor substrate; and forming a lower electrode disposed on the oxidation barrier pattern so that a top surface area of the oxidation barrier pattern is substantially equal to a bottom surface area of the lower electrode.

In particular embodiments, the lower electrode forming step may include: (a) forming a layer on the oxidation barrier pattern, the layer having a recess with a bottom that is sized to be substantially coextensive with a top surface of the oxidation barrier pattern; and (b) applying a conductive layer in the recess to thereby form the lower electrode.

### Brief Description of the Drawings

**FIG. 1** and **FIG. 2** are cross-sectional views of a MIM capacitor for explaining a prior art method for forming a lower electrode of a conventional MIM capacitor.



**FIG. 3** is a cross-sectional view of a MIM capacitor for explaining another prior art method for forming a lower electrode of a conventional MIM capacitor.

**FIG. 4** is a cross-sectional view of a semiconductor device which includes a MIM capacitor according to embodiments of the present invention.

5        **FIG. 5** through **FIG. 10** are cross-sectional views of a semiconductor device which includes features of and/or used in forming MIM capacitor according to embodiments of the present invention.

### Detailed Description

10        The present invention will now be described more fully hereinafter with reference to the accompanying drawings, in which embodiments of the invention are shown. The invention may, however, be embodied in different forms and should not be construed as limited to the embodiments set forth herein. Rather, these  
15        embodiments are provided so that this disclosure will be thorough and complete, and will fully convey the scope of the invention to those skilled in the art. In the drawings, the thickness of layers and regions may be exaggerated for clarity. It will also be understood that when a layer is referred to as being "on" another layer or substrate, it can be directly on the other layer or substrate, or intervening layers, films, coatings and the like may also be present unless the word "directly" is used which  
20        indicates that the feature or layer directly contacts the feature or layer. Like numbers refer to like elements throughout. In addition, spatially relative terms, such as "beneath", "below", "lower", "above", "upper" and the like, may be used herein for ease of description to describe one element or feature's relationship to another element(s) or feature(s) as illustrated in the figures. It will be understood that the  
25        spatially relative terms are intended to encompass different orientations of the device in use or operation in addition to the orientation depicted in the figures. For example, if the device in the figures is turned over, elements described as "below" or "beneath" other elements or features would then be oriented "above" the other elements or features. Thus, the exemplary term "below" can encompass both an orientation of  
30        above and below. The device may be otherwise oriented (rotated 90 degrees or at other orientations) and the spatially relative descriptors used herein interpreted accordingly.

A semiconductor device including a MIM capacitor **100** according to

embodiments of the present invention is now described below with reference to **FIG. 4**.

Referring to **FIG. 4**, first (shown as a lower) interlayer dielectric **104** and an etch-stop layer **105** are sequentially stacked on a semiconductor substrate **101**. A buried contact plug **107** extends through the etch-stop layer **105**, where used, and the first interlayer dielectric **104** to be electrically connected to a predetermined region of the semiconductor substrate **101**. The term "buried" means that the body of the contact plug extends at least partially a distance into the interlayer dielectric so as to provide at least a portion of an electrical path between the semiconductor substrate **101** and the lower electrode **117a**. The etch-stop layer **105** is optional. The first interlayer dielectric **104** may be made of silicon oxide. The buried contact plug **107** may be made of a conductive material such as, for example, doped polysilicon or tungsten (W). The etch-stop layer **105** may be made of an insulating material (*e.g.*, silicon nitride) having an etch selectivity with respect to the first interlayer dielectric **104**. The term "etch selectivity" means that the material or layer is resistant to removal during exposure to an etch removal process (*i.e.*, less sensitive or susceptible than the target etch-removable material or layer so that the non-target material or layer remains substantially intact relative to the target material or layer).

Still referring to **FIG. 4**, an oxidation barrier pattern **110a** is disposed on the top or upper surface of the buried contact plug **107**. A lower electrode **117a** is configured so that a bottom portion thereof is disposed on the upper surface of the oxidation barrier pattern **110a**. A predetermined region of a bottom side of the oxidation barrier pattern **110a** is electrically connected to the top surface of the buried contact plug **107**. The top surface area of the oxidation barrier pattern **110a** is substantially equal to a bottom surface area of the lower electrode **117a**. Namely, the top surface of the oxidation barrier pattern **110a** contacts substantially an entire bottom of (*i.e.*, is substantially coextensive with) the lower electrode **117a** and the oxidation barrier pattern **110a** and the lower electrode **117a** are electrically connected to each other. In certain embodiments, the lower electrode **117a** may be configured as a cylindrical electrode.

In certain embodiments, as shown in **FIG. 4**, an external sidewall **117w** of the lower electrode **117a** and a sidewall **110w** of the corresponding oxidation barrier pattern **110a** are spatially aligned so that the outer perimeters thereof are disposed in a beeline or substantially straight line. Stated differently, in particular embodiments, the

bottom outermost opposing sides of a respective lower electrode **117a** of a MIM capacitor terminate into the corresponding underlying sidewalls of the corresponding oxidation barrier pattern **110a** so as to jointly define an outermost perimeter profile with two spaced apart substantially vertical lines when viewed in cross-section.

5 Accordingly, the lower electrode **117a** may have larger area than a conventional lower electrode. As a result, the capacitor having the lower electrode **117a** may have a higher capacitance than a capacitor having the conventional lower electrode.

In certain embodiments, the oxidation barrier pattern **110a** comprises a material resistant to an oxidation process, *e.g.*, conductive metal nitride such as TiN, TaN, TiAlN, WN, and so forth. The lower electrode **117a** may comprise a suitable conductive material, such as, for example, noble metals and/or conductive compounds containing noble materials. The noble metals include, for example, palladium (Pd), ruthenium (Ru), platinum (Pt), and iridium (Ir). An exemplary conductive compound containing a noble metal is iridium dioxide (IrO<sub>2</sub>).

15 Still referring to **FIG. 4**, an upper electrode **122** is disposed over the lower electrode **117a** with a dielectric film **120** interposed therebetween. The capacitor **100** comprises the lower electrode **117a**, the dielectric film **120**, and the upper electrode **122**.

In certain embodiments, the upper electrode **122** can comprise a suitable conductive material(s) such as noble metals and/or conductive compounds containing the noble metals. The noble metals include, for example, palladium (Pd), ruthenium (Ru), platinum (Pt), and iridium (Ir). An exemplary conductive compound containing a noble metal is iridium dioxide (IrO<sub>2</sub>).

The dielectric film **120** may comprise a high dielectric constant ("high-k") dielectric material or substance having a higher dielectric constant that is greater than that of ONO (oxide-nitride-oxide). In certain embodiments, the dielectric film **120** is made of, for example, aluminum oxide (Al<sub>2</sub>O<sub>3</sub>) or hafnium oxide (HfO<sub>2</sub>). In certain embodiments, the capacitor **100**, typically having the high-k dielectric film **120**, can be used as a capacitor constituting a unit cell of a DRAM memory device. Unlike conventional unit cell capacitors of a DRAM device, the dielectric film **120** can comprise a ferroelectric substance such as PZT, SBT, BLT or combinations thereof. In particular embodiments, the capacitor **100** which may have the ferroelectric dielectric film **120**, is used as a capacitor constituting a unit cell of a ferroelectric memory device. As such, the unit memory cell may include a transistor in



communication with the capacitor.

A method of fabricating a semiconductor device including a MIM capacitor according to embodiments of the present invention is now described below with reference to **FIG. 5** through **FIG. 10**.

5 Referring to **FIG. 5**, a device isolation layer **102** is formed at a semiconductor device to define an active region. The device isolation layer **102** may be a trench isolation layer. Impurities are selectively implanted into the active region to form an impurity diffusion layer **103**. The impurity diffusion layer **103** may be a source/drain region of a transistor (not shown). The first interlayer dielectric **104** and the  
10 (optional) etch-stop layer **105** are sequentially stacked on the impurity diffusion layer **103**. In certain embodiments, the first interlayer dielectric **104** may comprise silicon oxide, and, as discussed above, where used, the etch-stop layer **105** may be made of an insulating material having an etch selectivity with respect to silicon oxide, *e.g.*, silicon nitride. The buried contact plug **107** is formed through the etch-stop layer **105**  
15 and the first interlayer dielectric **104** to be connected to a predetermined region of the impurity diffusion layer **103**. The buried contact plug **107** may comprise a conductive material such as, for example, doped polysilicon or tungsten (W). An oxidation barrier layer **110** and a capping layer **112** are sequentially stacked over the surface of the semiconductor substrate **101** including over the buried contact plug **107**. The  
20 oxidation barrier layer **110** can comprise a conductive material which is strongly resistant to oxidation, *e.g.*, conductive metal nitride such as TiN, TaN, TiAlN, and/or WN. The capping layer **112** may be made of a material having an etch selectivity with respect to the oxidation barrier layer **110**, *e.g.*, silicon nitride.

Referring to **FIG. 6** and **FIG. 7**, the capping layer **112** and the oxidation barrier  
25 layer **110** can be successively patterned to form a respective oxidation barrier layer pattern **110a** and a capping layer pattern **112a** which are, as described above, sequentially stacked. The oxidation barrier layer pattern **110a** covers a top surface of the buried contact plug **107**, *i.e.*, is electrically connected to the buried contact plug **107**. In view of the design constraint, the oxidation barrier layer pattern **110a** may be  
30 formed to provide a plurality of proximately positioned lower electrode platforms **110p**, each having a width " $W_1$ " that can be substantially the same width as the bottom of the lower electrode **117a** (**FIG. 4**). Adjacent ones of the oxidation barrier layers **110a** can be minimally spaced apart from each other. The spacing may be such that a distance " $W_2$ " separates adjacent barrier layer patterns **110a**.

A mold insulating layer **114** is formed over the surface of the stacked semiconductor substrate **101** including the capping layer pattern **112a** and the oxidation barrier layer pattern **110a**. The mold insulating layer **114** can be made of an insulating material having an etch selectivity with respect to the material forming the capping layer pattern **112a**. In addition, the mold insulating layer **114** can have an etch selectivity with respect to the material forming the oxidation barrier layer pattern **110a** and the material forming the etch-stop layer **105**. The mold insulating layer **114** may be made of, for example, silicon oxide.

By means of a suitable material removal process, such as, but not limited to, an etch-back or chemical mechanical polishing (CMP) technique, the mold insulating layer **114** can be planarized down to a top surface of the capping layer pattern **112a** as shown in **FIG. 7**.

Referring to **FIG. 8** and **FIG. 9**, the exposed capping layer pattern **112a** is removed and/or etched down to a top surface of the oxidation barrier layer pattern **110a**. As a result, the exposed capping layer pattern **112a** is removed to form a self-aligned lower electrode recess **115**. By removing the capping layer pattern **112a**, a void region corresponding to where the capping layer pattern **112a** was disposed becomes the lower electrode recess **115**. A sidewall **115w** of the lower electrode recess **115** is formed by the adjacent portion of the mold insulating layer **114**, and the lower electrode recess **115** can expose the entire top surface (the lower electrode platform **110p**) of the oxidation barrier layer pattern **110a**.

Referring to **FIG. 8**, a lower electrode layer **117** is conformably formed over the exposed portions of the stacked layers residing on the semiconductor substrate **101** including over the top, bottom and sidewalls of the lower electrode recess **115**. A sacrificial insulating layer **119** is formed over the lower electrode layer **117** in an amount sufficient to fill the lower electrode recess **115**. In certain embodiments, the lower electrode layer **117** comprises a conductive material such as noble metals and conductive compounds containing the noble metals. As described above, the noble metals include, for example, palladium (Pd), ruthenium (Ru), platinum (Pt), and iridium (Ir). One exemplary conductive compound containing a noble metal is iridium dioxide (IrO<sub>2</sub>). The sacrificial insulating layer **119** may comprise silicon nitride.

Referring to **FIG. 9**, the sacrificial insulating layer **119** and the lower electrode layer **117** are planarized down to a top surface of the mold insulating layer **114** to

form the lower electrode **117a** and a sacrificial insulating layer pattern **119a**. The insulating layer **119** resides over the lower electrode layer **117** (*i.e.*, they are sequentially stacked) in the lower electrode recess **115**. Due to the configuration of the lower electrode recess **115**, a bottom side of the lower electrode **117a** contacts substantially the entire top surface of a corresponding oxidation barrier pattern **110a**. That is, the bottom surface area of the lower electrode **117a** is substantially equal to a top surface area of the oxidation barrier layer pattern **110a**. Thus, the lower electrode **117a** can have an increased area than a conventional lower electrode. As a result, a capacitance of the capacitor having the lower electrode **117a** configured in this manner can increase.

Referring to **FIG. 10**, the sacrificial insulating layer pattern **119a** and the planarized mold insulating layer **114** can be removed, typically etched, to expose the electrode layer **117** and the etch-stop layer **105**. The etch removal can be carried out with any suitable etch removal process, and in certain embodiments is an isotropic etch that may be conducted by, for example, a wet etch. After this operation(s), inside and external surfaces of the sidewall(s) and the inner surface of the bottom or floor of the lower electrode **117a** are exposed.

A dielectric film **120** can then be conformably formed over the exposed surface (typically the entire surface) of the stacked configuration overlying and/or the semiconductor substrate **101** where the etch-stop layer **105** is exposed. The upper electrode **122** is formed on and/or over the dielectric film **120** above the lower electrode **117a**. The capacitor **100** includes the lower electrode **117a**, the dielectric film **120**, and the upper electrode **122**.

As described above, the dielectric film **120** may comprise a high-k dielectric material that has a higher dielectric constant than ONO (oxide-nitride-oxide). For example, the high-k dielectric material can be aluminum oxide ( $\text{Al}_2\text{O}_3$ ) and/or hafnium oxide ( $\text{HfO}_2$ ). As also described above, in certain embodiments, a capacitor having the high-k dielectric film may be used as a capacitor constituting a unit cell of a DRAM memory device. Unlike prior unit cells of DRAM memory devices, the dielectric film **120** may be made of and/or comprise a ferroelectric material such as PZT, SBT, BLT or combinations thereof. In addition, in certain embodiments, a capacitor having the ferroelectric dielectric film **120** may be used as a capacitor constituting a unit cell of a ferroelectric memory device.

In certain embodiments and as also discussed above, the upper electrode **122**

is made of one or more conductive materials such as noble metals and/or conductive compounds containing the noble metals. The noble metals include, for example, palladium (Pd), ruthenium (Ru), platinum (Pt), and iridium (Ir). An exemplary conductive compound containing a noble metal is, for example, iridium dioxide  
5 (IrO<sub>2</sub>).

In the drawings and specification, there have been disclosed embodiments of the invention and, although specific terms are employed, they are used in a generic and descriptive sense only and not for purposes of limitation, the scope of the invention being set forth in the following claims. Thus, the foregoing is illustrative of  
10 the present invention and is not to be construed as limiting thereof. Although a few exemplary embodiments of this invention have been described, those skilled in the art will readily appreciate that modifications are possible in the exemplary embodiments without materially departing from the novel teachings and advantages of this invention. Accordingly, all such modifications are intended to be included within the  
15 scope of this invention as defined in the claims. In the claims, means-plus-function clauses, where used, are intended to cover the structures described herein as performing the recited function and not only structural equivalents but also equivalent structures. Therefore, it is to be understood that the foregoing is illustrative of the present invention and is not to be construed as limited to the specific embodiments  
20 disclosed, and that modifications to the disclosed embodiments, as well as other embodiments, are intended to be included within the scope of the appended claims. The invention is defined by the following claims, with equivalents of the claims to be included therein.